3DG140

NPN Silicon High Frequency Low Power Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	Test Condition
Total Dissipation	P_{tot}	mW	100	Ta=25°C
Max. Collector Current	I_{CM}	mA	15	
Junction Temperature	T_{jm}	°C	175	
Storage Temperature	T_{stg}	°C	-55~+175	
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	20	I_C=0.1mA
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	15	
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	4	I_E=0.05mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.35	I_C=10mA I_B=1mA
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	1.0	
C-E Leakage Current	I_{CEO}	uA	0.1	V_{CE}=6V
E-B Leakage Current	I_{EBO}	uA	0.1	V_{EB}=1.5V
DC Current Gain	h_{FE}		25~180	V_{CE}=6V, I_C=1mA
Transition frequency	f_T	MHz	400	V_{CE}=6V, I_C=1mA f=100MHz

Outline and Dimensions: